

Yijin Zhang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

30
papers

3,450
citations

18
h-index

31
g-index

31
ext. papers

3,945
ext. citations

11.7
avg, IF

5.32
L-index

#	Paper	IF	Citations
30	Switchable out-of-plane shift current in ferroelectric two-dimensional material CuInP2S6. <i>Applied Physics Letters</i> , 2022 , 120, 013103	3.4	0
29	In situ Raman spectroscopy across superconducting transition of liquid-gated MoS2. <i>Applied Physics Letters</i> , 2022 , 120, 053106	3.4	
28	Subband-resolved momentum-conserved resonant tunneling in monolayer graphene/h-BN/ABA-trilayer graphene small-twist-angle tunneling device. <i>Applied Physics Letters</i> , 2022 , 120, 083102	3.4	1
27	Defect-assisted tunneling spectroscopy of electronic band structure in twisted bilayer graphene/hexagonal boron nitride moiré superlattices. <i>Applied Physics Letters</i> , 2022 , 120, 203103	3.4	
26	Resonant Tunneling Due to van der Waals Quantum-Well States of Few-Layer WSe in WSe/h-BN/p-MoS Junction. <i>Nano Letters</i> , 2021 , 21, 3929-3934	11.5	5
25	Ambipolar device simulation based on the drift-diffusion model in ion-gated transition metal dichalcogenide transistors. <i>Npj Computational Materials</i> , 2020 , 6,	10.9	2
24	Enhanced intrinsic photovoltaic effect in tungsten disulfide nanotubes. <i>Nature</i> , 2019 , 570, 349-353	50.4	86
23	Superconductivity in Pristine 2H_{a}-MoS_{2} at Ultrahigh Pressure. <i>Physical Review Letters</i> , 2018 , 120, 037002	7.4	62
22	Electric-field Control of Electronic States in WS2 Nanodevices by Electrolyte Gating. <i>Journal of Visualized Experiments</i> , 2018 ,	1.6	1
21	Optoelectronic response of a WS 2 tubular p - n junction. <i>2D Materials</i> , 2018 , 5, 035002	5.9	26
20	Exciton Hall effect in monolayer MoS. <i>Nature Materials</i> , 2017 , 16, 1193-1197	27	93
19	Extended Polymorphism of Two-Dimensional Material. <i>Nano Letters</i> , 2017 , 17, 5567-5571	11.5	20
18	Potential Profile of Stabilized Field-Induced Lateral p-n Junction in Transition-Metal Dichalcogenides. <i>ACS Nano</i> , 2017 , 11, 12583-12590	16.7	20
17	Robustly protected carrier spin relaxation in electrostatically doped transition-metal dichalcogenides. <i>Physical Review B</i> , 2017 , 95,	3.3	11
16	Gate-Optimized Thermoelectric Power Factor in Ultrathin WSe2 Single Crystals. <i>Nano Letters</i> , 2016 , 16, 2061-5	11.5	95
15	High circular polarization in electroluminescence from MoSe2. <i>Applied Physics Letters</i> , 2016 , 108, 073107	3.4	29
14	Memristive phase switching in two-dimensional 1T-TaS2 crystals. <i>Science Advances</i> , 2015 , 1, e1500606	14.3	156

13	2D crystals of transition metal dichalcogenide and their iontronic functionalities. <i>2D Materials</i> , 2015 , 2, 044004	5.9	23
12	Superconductivity Series in Transition Metal Dichalcogenides by Ionic Gating. <i>Scientific Reports</i> , 2015 , 5, 12534	4.9	170
11	Controlling charge-density-wave states in nano-thick crystals of 1T-TaS2. <i>Scientific Reports</i> , 2014 , 4, 73024.9	4.9	102
10	Electrically switchable chiral light-emitting transistor. <i>Science</i> , 2014 , 344, 725-8	33.3	570
9	Valley-dependent spin polarization in bulk MoS2 with broken inversion symmetry. <i>Nature Nanotechnology</i> , 2014 , 9, 611-7	28.7	306
8	Fabrication of stretchable MoS2 thin-film transistors using elastic ion-gel gate dielectrics. <i>Applied Physics Letters</i> , 2013 , 103, 023505	3.4	75
7	Formation of a stable p-n junction in a liquid-gated MoS2 ambipolar transistor. <i>Nano Letters</i> , 2013 , 13, 3023-8	11.5	178
6	Ambipolar transport in MoS2 based electric double layer transistors. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1549, 73-78		
5	Superconducting dome in a gate-tuned band insulator. <i>Science</i> , 2012 , 338, 1193-6	33.3	755
4	Ambipolar MoS2 thin flake transistors. <i>Nano Letters</i> , 2012 , 12, 1136-40	11.5	662
3	Gate-Induced Superconductivity in Layered-Material-Based Electric Double Layer Transistors. <i>Journal of Physics: Conference Series</i> , 2012 , 400, 022139	0.3	1
2	Nanosession: Superconductivity367-375		
1	Resonant Tunneling between Quantized Subbands in van der Waals Double Quantum Well Structure Based on Few-Layer WSe2. <i>Nano Letters</i> ,	11.5	1